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This listing of claims will replace all prior versions, and listings, of claims in the application.

Listing of Claims:

1-44. (cancelled)

semiconductor device, comprising:

providing a wafer for forming an integrated circuit thereon, the wafer having a main surface on which an integrated circuit is to be formed, a substantially circular contour portion surrounding said main surface, a curved positioning notch formed in said circular contour portion and connecting portions defined between said circular contour portion and said curved positioning notch;

wherein an outer peripheral part of said wafer is chamfered in a thickness direction by mechanical chamfering, and

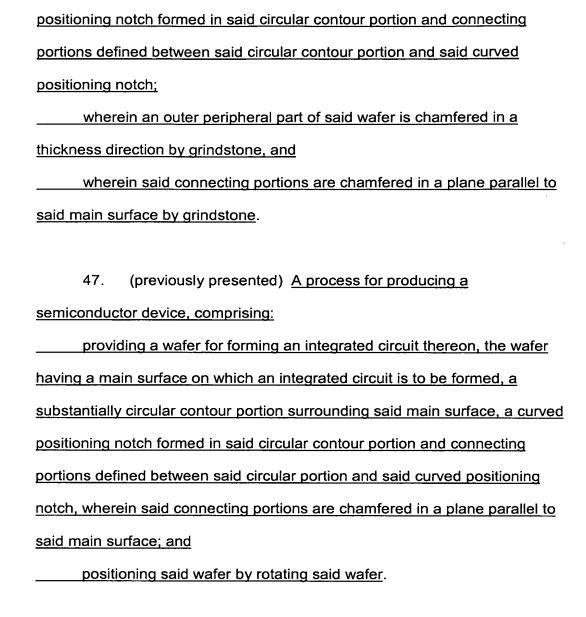
wherein said connecting portions are chamfered in a plane parallel to said main surface by mechanical chamfering.

46. (previously presented) A process for producing a semiconductor device, comprising:

providing wafer for forming an integrated circuit thereon, the wafer

having a main surface on which an integrated circuit is to be formed, a

substantially circular contour portion surrounding said main surface, a curved



- 48. (previously presented) A process for producing a semiconductor device according to claim 47, wherein, in the positioning step, positioning said wafer by using photoelectric elements.
- 49. (previously presented) A process for producing a semiconductor device according to claim 48, wherein an outer peripheral part

of said wafer is chamfered in a thickness direction by mechanical chamfering,

and

wherein said connecting portions are chamfered in a plane parallel to
said main surface by mechanical chamfering.

- 50. (previously presented) A process for producing a semiconductor device according to claim 48, wherein an outer peripheral part of said wafer is chamfered in a thickness direction by grindstone, and wherein said connecting portions are chamfered in a plane parallel to said main surface by grindstone.
- 51. (previously presented) A process for producing a semiconductor device according to claim 47, wherein, in the positioning step, positioning said wafer by optical means.
- 52. (previously presented) A process for producing a semiconductor device according to claim 47, wherein an outer peripheral part of said wafer is chamfered in a thickness direction by mechanical chamfering, and wherein said connecting portions are chamfered in a plane parallel to
- 53. (previously presented) A process for producing a semiconductor device according to claim 47, wherein an outer peripheral part of said wafer is chamfered in a thickness direction by grindstone, and

said main surface by mechanical chamfering.

wherein said connecting portions are chamfered in a plane parallel to said main surface by grindstone.

54-60. (cancelled)